

Claim Listing

1.-82. (Canceled)

83. (Previously presented) A thin film device comprising: a metal sulfide layer selected from the group consisting of manganese sulfide (MnS), magnesium sulfide (MgS), and calcium sulfide (CaS), which is formed on a single crystal silicon substrate; and a thin film comprising an ionic compound, which is formed on the metal sulfide layer, wherein said single crystal silicon is a single crystal silicon (100), and said ionic compound thin film is an aluminum nitride (AlN) having a (1120) surface as its top surface.

84. (Previously presented) The thin film device as claimed in claim 83, further comprising an ionic compound having a (1120) thin film, which has a (1120) surface formed by epitaxial growth as its top surface, and is formed on said aluminum nitride (AlN) layer having the (1120) surface as its top surface, or via another intermediate layer.

85. (Previously presented) The thin film device as claimed in claim 84, wherein said compound thin film comprises a gallium nitride (GaN) thin film having a (1120) surface as its top surface.

86. (Canceled)

87. (Canceled)

88. (Canceled)

89. (Canceled)

90. (Canceled)

91. (Canceled)

92. (Canceled)

93. (Canceled)

94. (Canceled)